



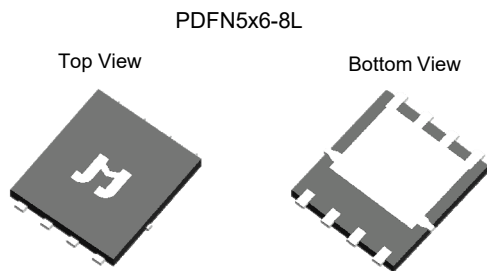
60V 2.4mΩ N-Ch Power MOSFET

Features

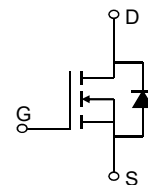
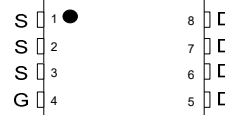
- Ultra-low ON-resistance,  $R_{DS(ON)}$
- Low Gate Charge,  $Q_g$
- 100% UIS and  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant
- AEC-Q101 Qualified for Automotive Applications

Product Summary

Parameter	Value	Unit
$V_{DS}$	60	V
$V_{GS(th\_Typ)}$	2.8	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(1)</sup>	157	A
$R_{DS(ON\_Typ)}$ (@ $V_{GS} = 10V$ )	2.4	mΩ



Pin Configuration  
Top View

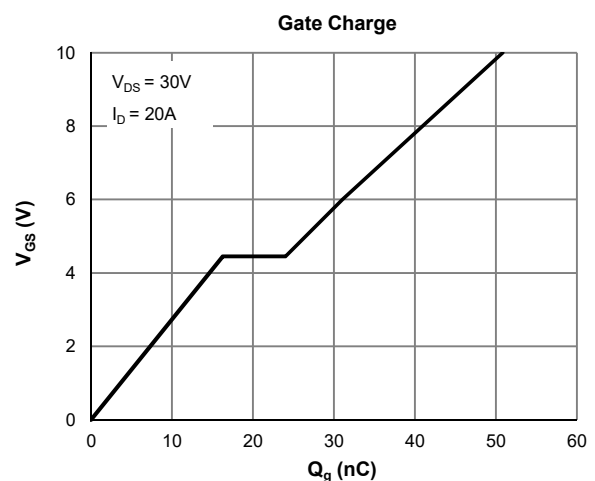
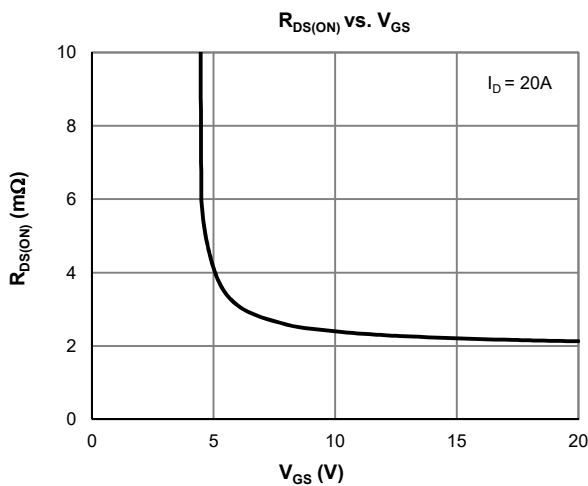


Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH0603BGQ-13	PDFN5x6-8L	8	SH0603BQ	1	-55 to 175	13-inch Reel	5000

Absolute Maximum Ratings (@  $T_A = 25^\circ C$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	60	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$I_D$	$T_C = 25^\circ C$	157
		$T_C = 100^\circ C$	111
Pulsed Drain Current <sup>(2)</sup>	$I_{DM}$	626	A
Avalanche Energy <sup>(3)</sup>	$E_{AS}$	338	mJ
Power Dissipation <sup>(4)</sup>	$P_D$	$T_C = 25^\circ C$	136
		$T_C = 100^\circ C$	68
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	°C



**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48\text{V}$ , $V_{GS} = 0\text{V}$			1.0	$\mu\text{A}$
					5.0	
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}$ , $V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2.2	2.8	3.4	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$ , $I_D = 20\text{A}$		2.4	3.0	$\text{m}\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}$ , $I_D = 20\text{A}$		81		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}$ , $V_{GS} = 0\text{V}$		0.65	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			136	A

**DYNAMIC PARAMETERS** <sup>(5)</sup>

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 30\text{V}$ , $f = 1\text{MHz}$		3549		pF
Output Capacitance	$C_{oss}$			959		pF
Reverse Transfer Capacitance	$C_{rss}$			38		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V}$ , $f = 1\text{MHz}$		1.6		$\Omega$

**SWITCHING PARAMETERS** <sup>(5)</sup>

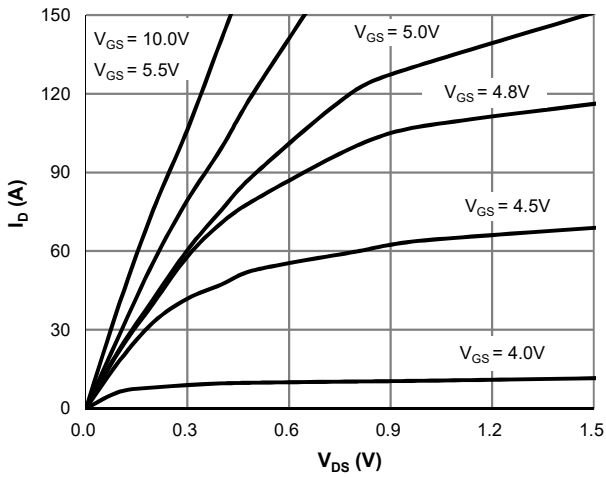
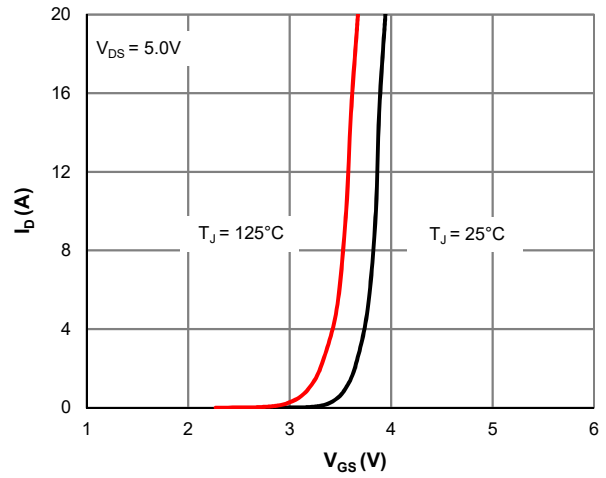
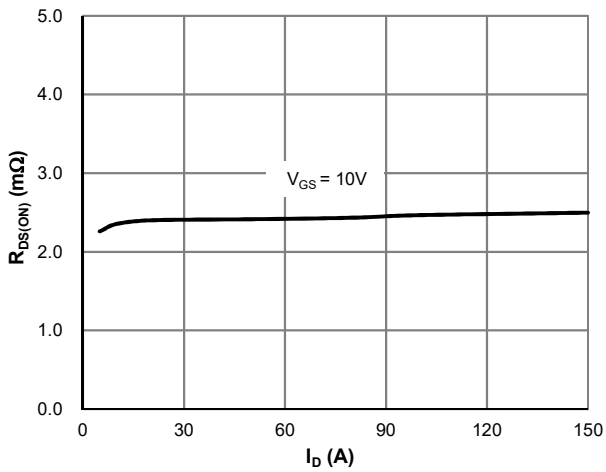
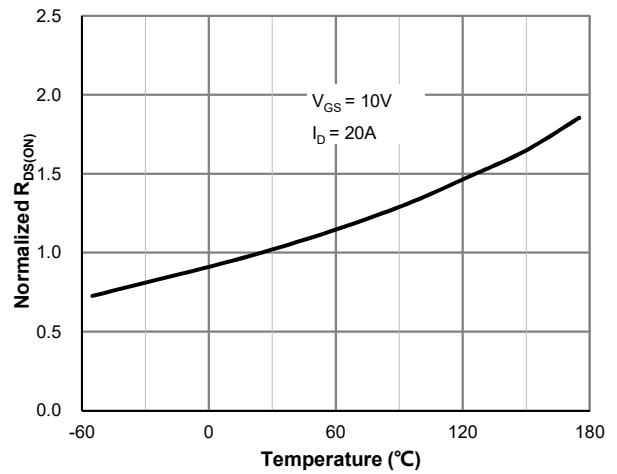
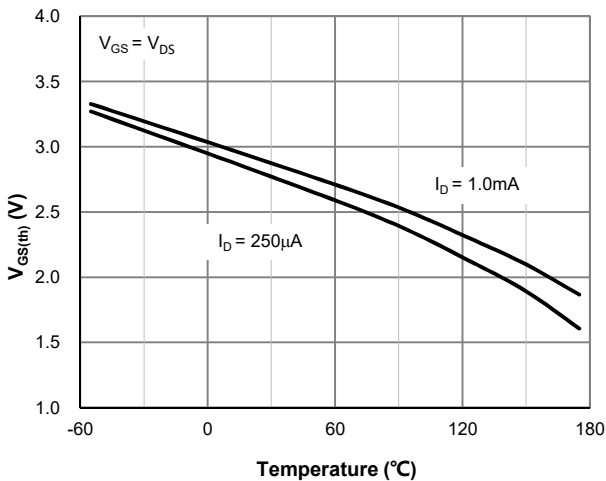
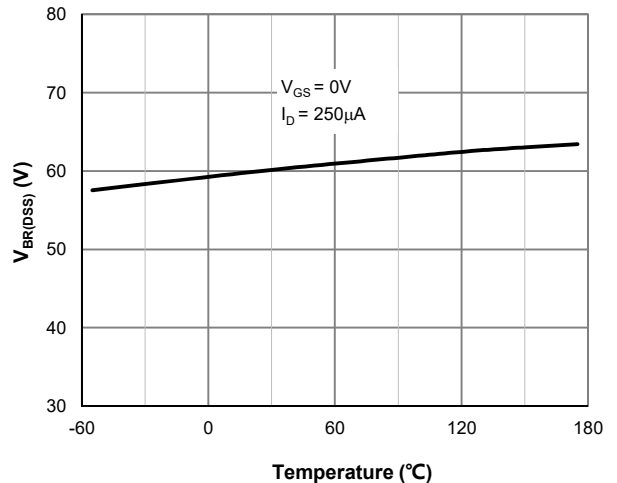
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0$ to $10\text{V}$ $V_{DS} = 30\text{V}$ , $I_D = 20\text{A}$		51		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$ )	$Q_g$			31		nC
Gate Source Charge	$Q_{gs}$			16.3		nC
Gate Drain Charge	$Q_{gd}$			7.7		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 30\text{V}$ $R_L = 1.5\Omega$ , $R_{GEN} = 6\Omega$		71		ns
Turn-On Rise Time	$t_r$			21		ns
Turn-Off DelayTime	$t_{D(off)}$			52		ns
Turn-Off Fall Time	$t_f$			85		ns
Body Diode Reverse Recovery Time	$t_{rr}$		$I_F = 20\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$		48	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 20\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$		49		nC

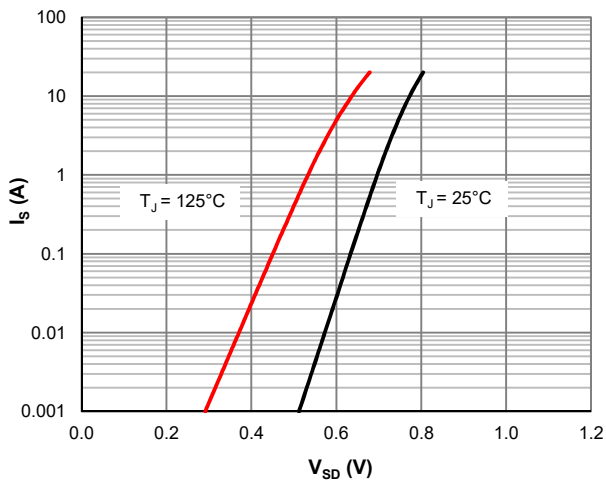
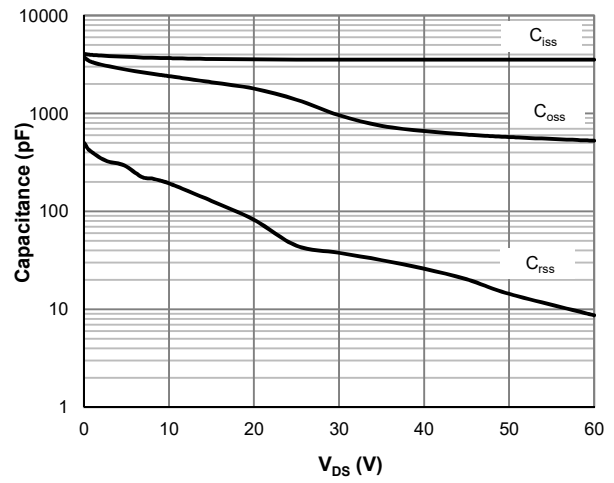
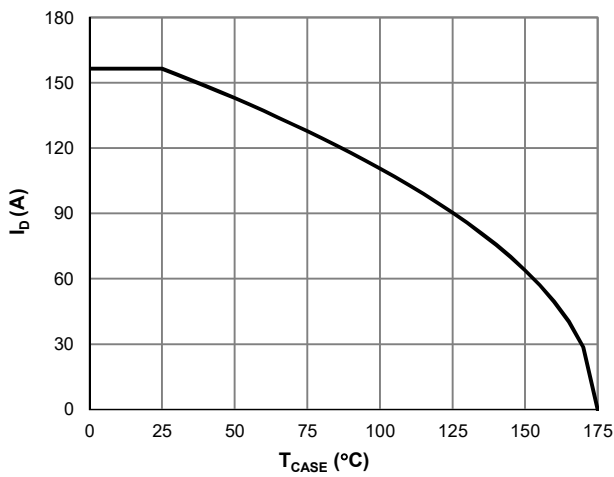
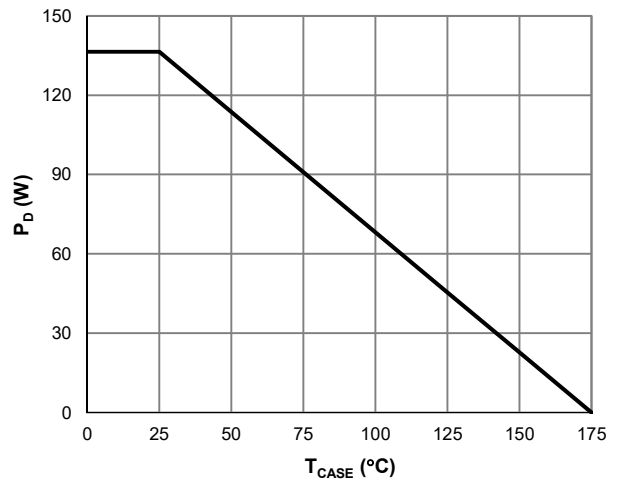
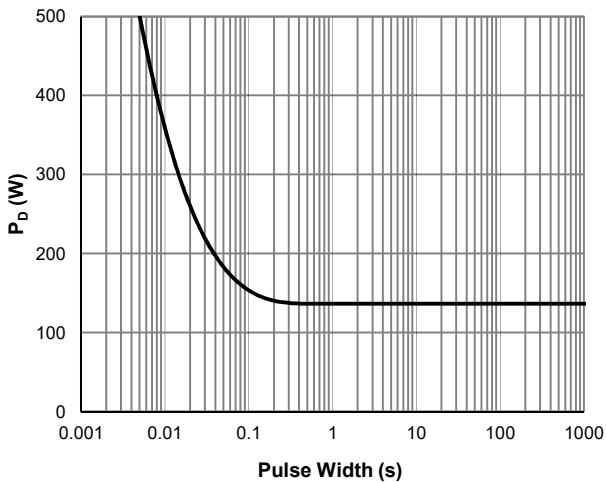
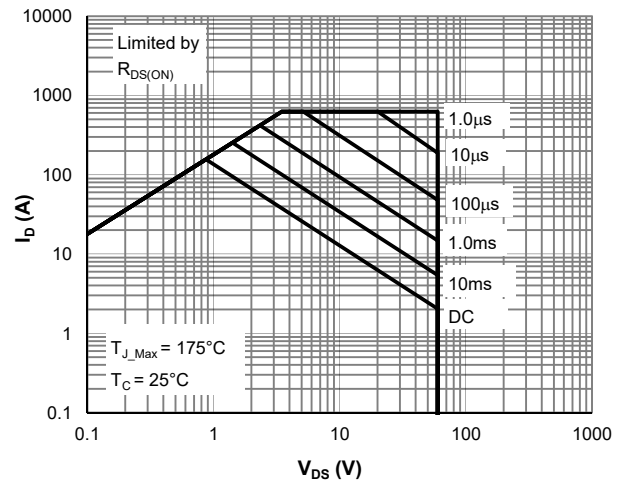
**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	52	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.1	1.2	$^\circ\text{C}/\text{W}$

**Notes:**

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J\_Max} = 175^\circ\text{C}$ .
3.  $E_{AS}$  of 338 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.0\text{mH}$ ,  $I_{AS} = 15\text{A}$ ,  $V_{GS} = 10\text{V}$ ,  $V_{DD} = 30\text{V}$ ; 100% test at  $L = 0.3\text{mH}$ ,  $I_{AS} = 40\text{A}$ .
4. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 175^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

**Typical Electrical & Thermal Characteristics**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**

**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

**Figure 5:  $V_{GS(th)}$  vs. Junction Temperature**

**Figure 6:  $V_{BR(DSS)}$  vs. Junction Temperature**

**Typical Electrical & Thermal Characteristics**

**Figure 7: Body-Diode Characteristics**

**Figure 8: Capacitance Characteristics**

**Figure 9: Current De-rating**

**Figure 10: Power De-rating**

**Figure 11: Single Pulse Power Rating, Junction-to-Case**

**Figure 12: Maximum Safe Operating Area**



### Typical Electrical & Thermal Characteristics

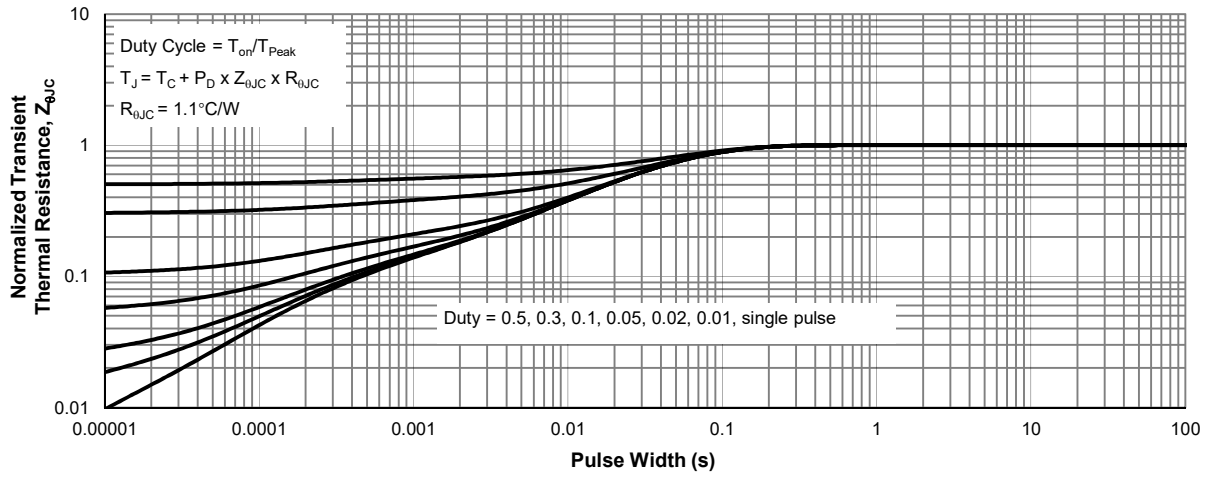
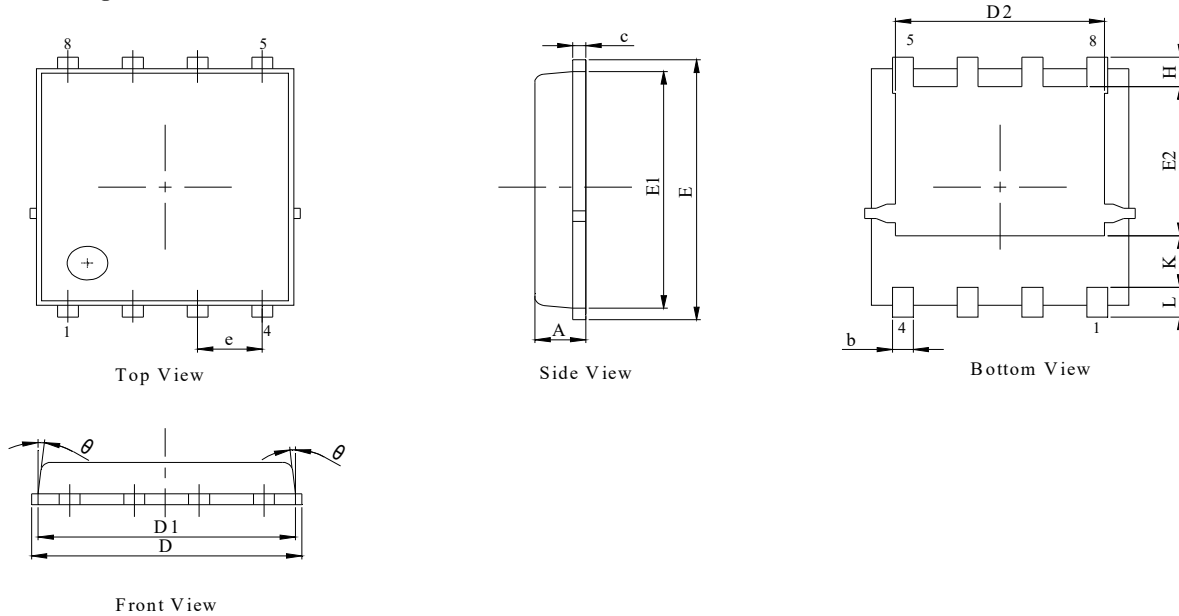
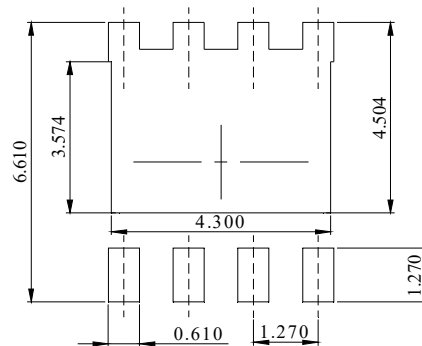


Figure 13: Normalized Maximum Transient Thermal Impedance

**PDFN5x6-8L Package Information**
**Package Outline**

**NOTES:**

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions  $D1$  and  $E1$  do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
c	0.20	0.25	0.30
D	5.00	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.42	3.53	3.63
e	1.27BSC		
H	0.60	0.70	0.80
L	0.50	0.70	0.80
K	1.23 REF		
$\theta$	-	-	10°

**Recommended Soldering Footprint**


DIMENSIONS: MILLIMETERS

单击下面可查看定价，库存，交付和生命周期等信息

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